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L11: (4) 10 and ("same" with orientation)
L12: (2898) grain and crystal$4 and (structure and
L13: (1255) 12 and (crystal$4 adj3 orientation)
L14: (129) 13 and cluster
L15: (39) (14 not 9) and ("same" with orientation)
L16: (15) 15 and grain.ab.
L17: (24) 15 not 16
L18: (5) (("6190949") or ("6150203") or ("5981974"))
Failed
Saved
(533) ogata-kiyoshi.in.
(56) takahara-yoichi.in.
(114) horikoshi-kazuhiko.in.
(11) yamaguchi-hironaru.in.
(37) ohkura-makoto.in.
(114) abe-hironobu.in.
(9) saitou-masakazu.in.
(185) kimura-yoshinobu.in.
(40) itoga-toshihiko.in.
(35) tamura-takuo.in.
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The screenshot displays the STN/EXPLORE interface. At the top, there are buttons for 'Search', 'Index', 'Browse', 'Query', and 'Clear'. Below these, a 'DBs' dropdown menu is set to 'USPAT, US-PQ-PUB, EPO, JPO, IBM, TDB'. The 'Default operator' is set to 'OR'. On the right, there are checkboxes for 'Print Results' and 'Highlight all hit terms initially'. The main search area contains the query '10 and ("same" with orientation)'. The results pane is empty, showing only a header for 'Number of Hits' and a table with columns for 'Number of Hits', 'Database', and 'Hit Count'.

	U	1	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XI
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040155295	20040812	15	Thin film transistor and display using the same	257/359	257/E21.41
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6657227 B2	20031202	14	Transistor with thin film active region having clusters of different crystal orientation	257/64	257/347; 257/352
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6452341 B1	20020917	33	EL display device, driving method thereof, and electronic equipment provided with the EL display device	315/169.1	315/169.2; 315/169.3
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6323515 B1	20011127	43	Non-volatile memory and semiconductor device	257/316	257/347; 257/350;